

# P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	$R_{DS(on)}(\Omega)$ $I_{D}(A)$				
- 100	$0.035$ at $V_{GS} = -10 \text{ V}$	- 39	11.7			
- 100	$0.038$ at $V_{GS} = -4.5 \text{ V}$	- 32	11.7			

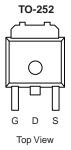
#### **FEATURES**

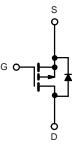
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
  Compliant to RoHS Directive 2002/95/EC



#### **APPLICATIONS**

- · Power Switch
- DC/DC Converters





P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> T <sub>C</sub> = 25 °C, unless otherwise noted						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V <sub>DS</sub>	- 100	V			
Gate-Source Voltage	V <sub>GS</sub>	± 20	7 v			
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	T <sub>C</sub> = 25 °C	L	- 39			
Continuous Diam Current (1) = 150 °C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	- 33.1			
Pulsed Drain Current		I <sub>DM</sub>	- 142	A		
Avalanche Current		I <sub>AS</sub>	- 28			
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	25.7	mJ		
	T <sub>C</sub> = 25 °C		88.4 <sup>b</sup>	14/		
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C <sup>c</sup>	$ P_{D}$ $-$	3.9	W		
Operating Junction and Storage Temperature Range		T <sub>.l</sub> , T <sub>sta</sub>	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	50	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	2.2	C/VV		

#### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub> V <sub>DS</sub> = 0 V, I <sub>D</sub> = - 250 μA - 100		- 100			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3.5	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
		V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V			- 1	μA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50		
		V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C			- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 15			Α	
	D	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3.6 A		0.035		Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 3.4 A		0.038			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 3.6 A		17		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			922		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -50 \text{ V}, f = 1 \text{ MHz}$		85			
Reverse Transfer Capacitance	C <sub>rss</sub>	]		61			
Total Cata Charma <sup>C</sup>	Q <sub>g</sub>	V <sub>DS</sub> = - 50 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3.6 A		28.2		nC	
Total Gate Charge <sup>c</sup>				19.3			
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = -50 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -3.6 \text{ A}$		5.1			
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			5.4			
Gate Resistance	R <sub>g</sub>	f = 1 MHz	1.2	5.7	11.5	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			7	14		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -50 \text{ V}, R_L = 17.2 \Omega$		12	18		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ - 2.9 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		33	50	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>	1		9	18		
Drain-Source Body Diode Ratings a	nd Characteri	stics T <sub>C</sub> = 25 °C <sup>b</sup>					
Continuous Current	Is				- 39		
Pulsed Current	I <sub>SM</sub>				-142	A	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 2.9 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			50	75	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = - 2.9 A, dl/dt = 100 A/μs		- 4	- 6	Α	
Reverse Recovery Charge	Q <sub>rr</sub>	†		98	147	nC	

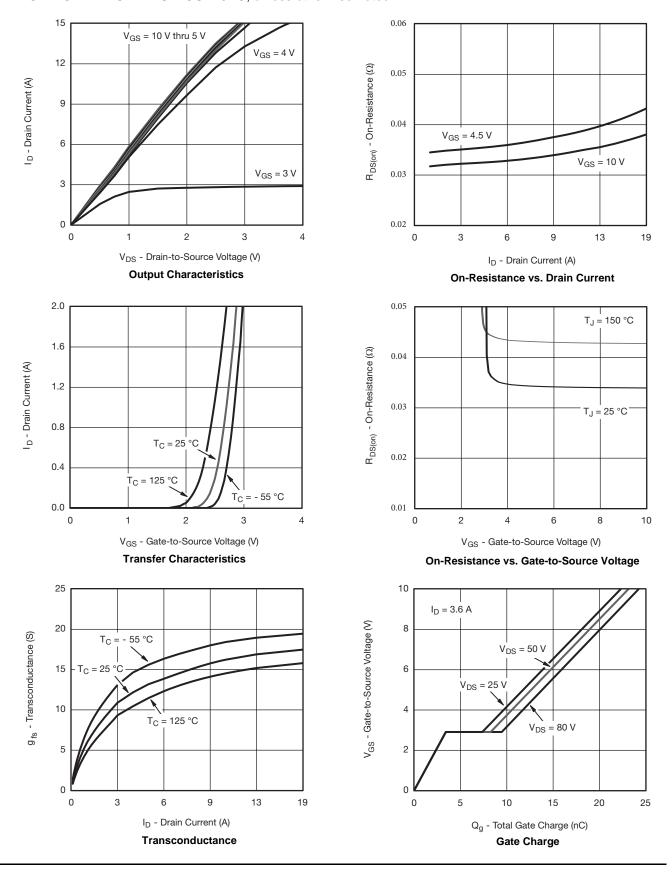
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

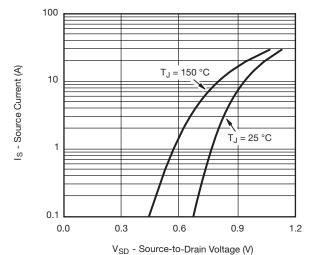


### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

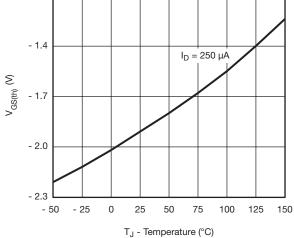




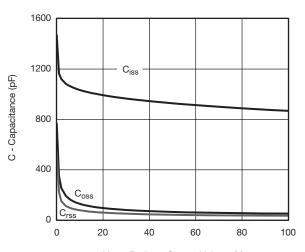
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

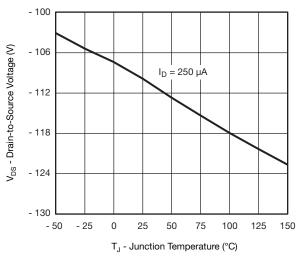


**Source-Drain Diode Forward Voltage** 

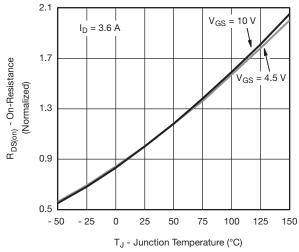


Threshold Voltage

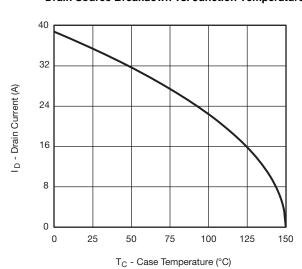




**Drain Source Breakdown vs. Junction Temperature** 

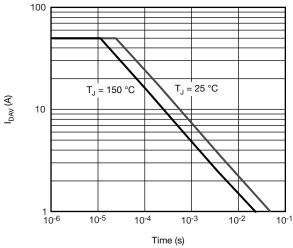


On-Resistance vs. Junction Temperature

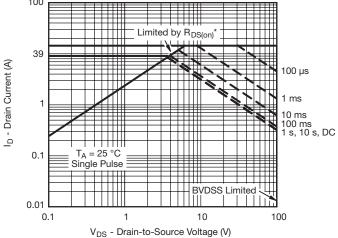


**Current Derating** 

# TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

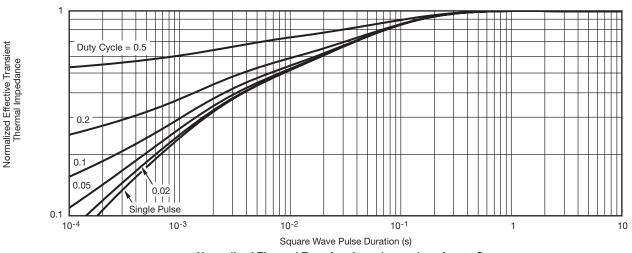


Single Pulse Avalanche Current Capability vs. Time



\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

#### Safe Operating Area

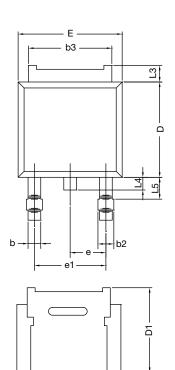


Normalized Thermal Transient Impedance, Junction-to-Case

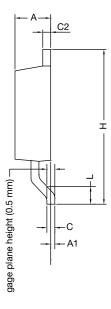




# **TO-252AA CASE OUTLINE**



E1



	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	-	0.205	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.14	1.52	0.045	0.060	
ECN: X12-0247-Rev. M, 24-Dec-12					

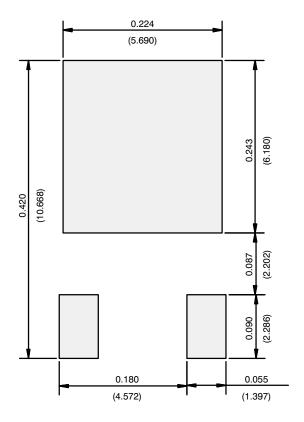
DWG: 5347

#### Note

• Dimension L3 is for reference only.



### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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